

**NPN Plastic-Encapsulate Transistors**
**Description**

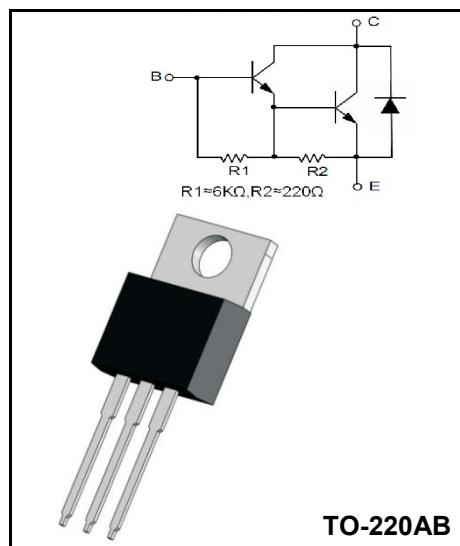
The devices are manufactured in planar technology with “base island” layout and monolithic Darlington configuration. The resulting transistors show exceptional high gain performance coupled with very low saturation voltage.

**Applications**

- General purpose linear and switching

**Features**

- Low collector-emitter saturation voltage
- Complementary to TIP125/126/127


**TO-220AB**
**Absolute Maximum Rating (Ta=25°C)**

Parameter	Symbol	Value			Unit
		TIP120	TIP121	TIP122	
Collector-Base Voltage	BV <sub>CBO</sub>	60	80	100	V
Collector-Emitter Voltage	BV <sub>CEO</sub>	60	80	100	V
Emitter-Base Voltage	BV <sub>EBO</sub>		5		V
Collector Current(DC)	I <sub>C</sub>		5		A
Collector Dissipation	P <sub>C</sub>	Ta = 25 °C		2	W
		Tc = 25 °C		65	
Junction Temperature	T <sub>j</sub>		150		°C
Storage Temperature	T <sub>stg</sub>		-65~150		°C

**Electrical Characteristics (Ta=25°C)**

Parameter	Symbol	Conditions	Value			Unit
			Min	Typ	Max	
Collector-Emitter Sustaining Voltage	V <sub>CEO(sus)</sub>	I <sub>C</sub> = 30mA, I <sub>B</sub> = 0	60 80 100			V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> = 60V, I <sub>E</sub> = 0 V <sub>CB</sub> = 80V, I <sub>E</sub> = 0 V <sub>CB</sub> = 100V, I <sub>E</sub> = 0			0.2	mA
Collector cut-off current	I <sub>CEO</sub>	V <sub>CE</sub> = 30V, I <sub>E</sub> = 0 V <sub>CE</sub> = 40V, I <sub>E</sub> = 0 V <sub>CE</sub> = 50V, I <sub>E</sub> = 0			0.5	mA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = 5V, I <sub>C</sub> = 0			2	mA
* DC current gain	h <sub>FE</sub>	V <sub>CE</sub> = 3V, I <sub>C</sub> = 0.5A V <sub>CE</sub> = 3V, I <sub>C</sub> = 3A	1000 1000			
* Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = 3A, I <sub>B</sub> = 12mA I <sub>C</sub> = 5A, I <sub>B</sub> = 20mA			2.0 4.0	V
* Base-Emitter ON Voltage	V <sub>BE(on)</sub>	V <sub>CE</sub> = 3V, I <sub>C</sub> = 3A			2.5	V
Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> = 10V, I <sub>E</sub> = 0, f = 0.1MHz			200	pF

\* Pulse Test : PW ≤ 300μs, Duty cycle ≤ 2%

Typical Characteristics

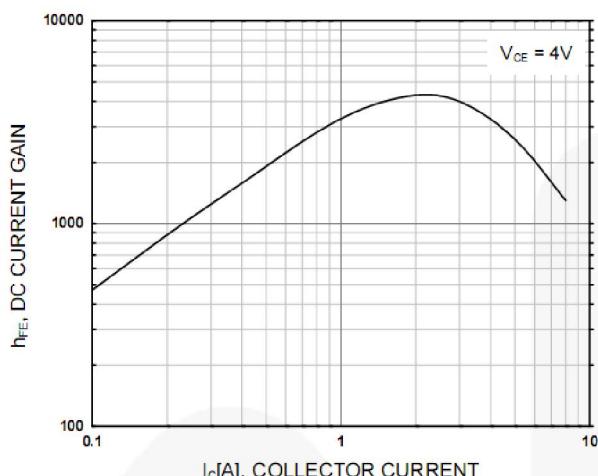


Figure 1. DC current Gain

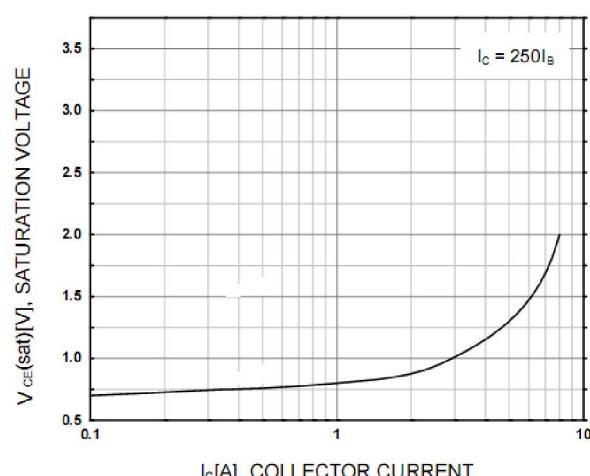


Figure 2. Collector-Emitter Saturation Voltage

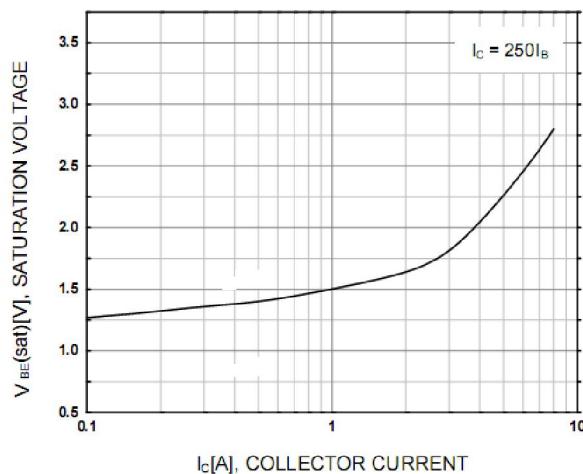


Figure 3. Base-Emitter Saturation Voltage

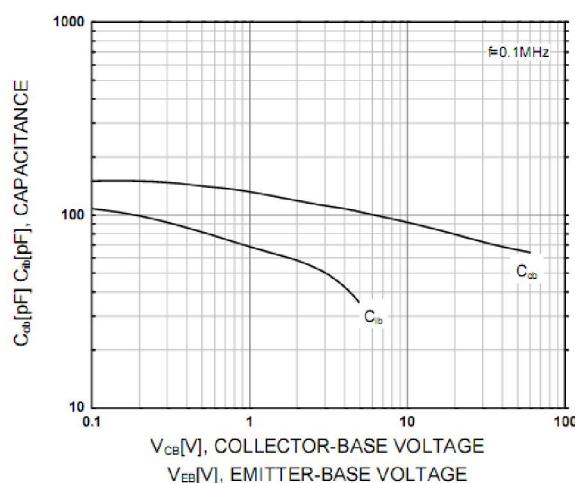


Figure 4. Output and Input Capacitance

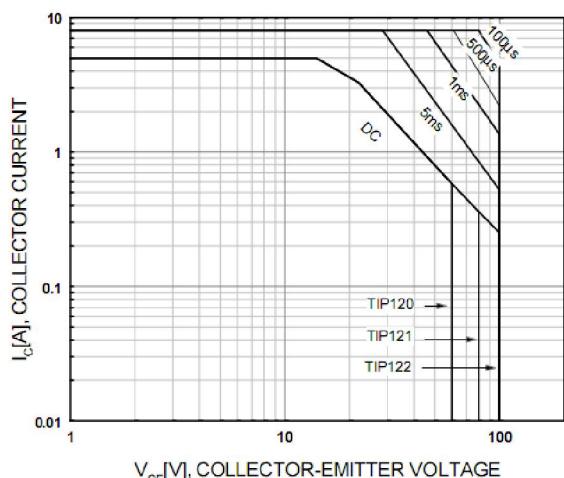


Figure 5. Safe Operating Area

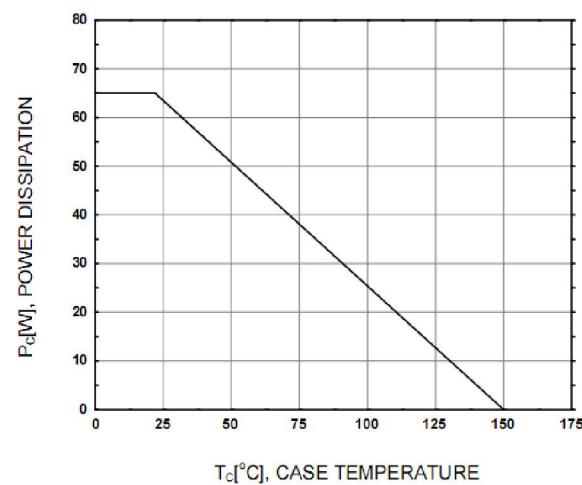
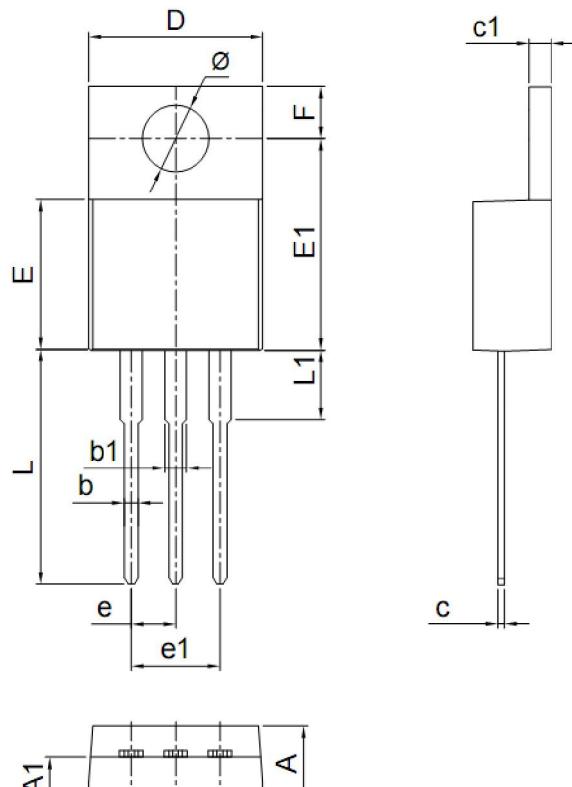


Figure 6. Power Derating

**Package Dimensions**


Symbol	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.34	4.67	0.171	0.184
A1	2.52	2.82	0.099	0.111
b	0.71	0.91	0.028	0.036
b1	1.17	1.37	0.046	0.054
c	0.30	0.50	0.012	0.020
c1	1.17	1.37	0.046	0.054
D	9.90	10.20	0.390	0.402
E	8.50	8.90	0.335	0.350
E1	12.00	12.50	0.472	0.492
e	2.44	2.64	0.096	0.104
e1	4.88	5.28	0.192	0.208
F	2.60	2.80	0.102	0.110
L	13.20	13.80	0.520	0.543
L1	3.80	4.20	0.150	0.165
Φ	3.60	3.96	0.142	0.156

**Product Specification Classification**

Part Number	Package	Marking	Pack
TIP120	TO-220AB	YFW TIP120 XXXXX	1000PCS/box
TIP121	TO-220AB	YFW TIP121 XXXXX	1000PCS/box
TIP122	TO-220AB	YFW TIP122 XXXXX	1000PCS/box